AMENDMENTS TO THE CLAIMS

1. (Cancelled).

2. (Currently Amended) A surface processing method comprising the steps of:

masking a portion of a susceptor (1) forming contact with a substrate (4),

applying a blasting process on said surface of a susceptor (1) that has SiO_2 as a main component, and

etching the surface of said susceptor; and

wherein said susceptor includes:

a susceptor main body (2), and

a stepped portion (3) provided on said susceptor main body (2) to support said substrate (4) from the bottom, having a size smaller than said substrate (4), said stepped portion (3) being masked in said masking step, wherein conduction at an end plane of the substrate (4) and the main body (2) can be prevented.

3. (Cancelled)

4. (Previously Presented) The surface processing method according to claim 2, further comprising the step of high pressure rinsing of the surface of said susceptor (1), prior to said step of blasting.

5. (Original) The surface processing method according to claim 2, wherein said step of blasting is carried out using SiO_2 or SiC.

6. (Previously Presented) The surface processing method according to claim 2, further comprising the step of high pressure rinsing the surface of said susceptor (1) after said etching.

7. (Currently Amended) A surface processing method of a glass jig that has SiO_2 as a main component, used in a neighborhood of a substrate and a wafer in a semiconductor formation process, a plasma display panel formation process, a plasma address liquid crystal formation process, and flat panel display formation process, comprising:

a first step of applying a blasting process on a surface of a subject to be processed,

a second step of etching the surface of said subject to be processed, and

a third step of cleaning said subject to be processed with one of means of:

(i) rinsing at high pressure,

(ii) rinsing with pure water and rinsing at high pressure;

wherein the method further comprises a step of masking a portion of a susceptor (1) forming contact with said substrate (4), prior to said first step; and

wherein said susceptor includes:

a susceptor main body (2), and

a stepped portion (3) provided on said susceptor main body (2) to support said substrate (4) from the bottom, having a size smaller than said substrate (4), said stepped portion (3) being masked in said masking step, wherein conduction at an end plane of the substrate (4) and the main body (2) can be prevented.

8. (Cancelled)

9. (Cancelled)

10. (Previously Presented) The surface processing method according to claim 7, further comprising the step of rinsing the surface of said susceptor (1) at high pressure, prior to said step of blasting.

11. (Previously Presented) A surface processing method comprising the steps of:

applying a blasting process on a surface of a susceptor (1) that has SiO_2 as a main component, and

etching the surface of said susceptor;

wherein the method further comprises another etching step being different from the first recited etching step and a step of high pressure rinsing the surface of said susceptor (1), and

wherein prior to said step of blasting said another etching step and said high pressure rinsing step are repeated.

12. (Previously Presented) A surface processing method of a glass jig that has SiO_2 as a main component, used in a neighborhood of a substrate and a wafer in a semiconductor formation process, a plasma display panel formation process, a plasma address liquid crystal formation process, and flat panel display formation process, comprising:

a first step of applying a blasting process on a surface of a subject to be processed,

a second step of etching the surface of said subject to be processed, and

a third step of cleaning said subject to be processed with one of means of:

(i) rinsing at high pressure,

(ii) rinsing with pure water and rinsing at high pressure;

wherein the method further comprises another etching step being different from said first recited etching step and a step of high pressure rinsing the surface of said susceptor (1), and

wherein prior to said step of blasting said another etching step and said high pressure rinsing step are repeated.